

# **30V P-Channel Enhancement Mode MOSFET**

### • General Description

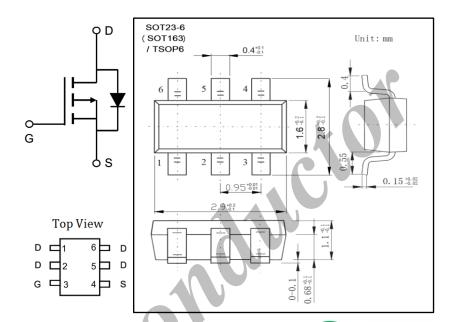
AP6405 combines advanced MOSFET technology with a low resistance package to provide extremely low  $R_{DS(\text{ON})}$ . This device is most suitable to load switch or PWM applications.

### Applications

- DC-DC converter for portable devices
- Load switch

# Product Summary

V <sub>DS</sub>	-30V
In (at $V_{GS} = -10V$ )	-5.0A
$R_{DS(ON)}$ (at $V_{GS} = -10V$ )	< 52mΩ
$R_{DS(ON)}$ (at $V_{GS} = -4.5V$ )	< 87mΩ







# • Absolute Maximum Ratings Ta = 25°C

Parameter		Symbol	Rating	Unit		
Drain-Source Voltage		$V_{\mathrm{DS}}$	-30	V		
Gate-Source Voltage		$V_{GS}$	±20	V		
Continuous Drain Current (T. 150 °C)	Ta = 25°C	T	-5	A		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	Ta = 70°C	$I_{\mathrm{D}}$	-4.2			
Pulsed Drain Current	ulsed Drain Current			]		
Power Dissipation	Ta = 25°C	$P_D$	2	W		
	Ta = 70°C	r <sub>D</sub>	1.3			
Junction and Storage Temperature Range		$T_J$ , $T_{STG}$	-55 to 150	°C		
Thermal Characteristics						
Thermal Resistance. Junction-to-Ambient	t ≤ 10s	D	62.5	°C/W		
	Steady-State	$R_{ heta JA}$	110			
Thermal Resistance. Junction-to-Lead		$R_{ heta JL}$	50			



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#### • Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static Parameters							
Drain-Source Breakdown Voltage	$V_{\rm DSS}$	I <sub>D</sub> =-250μA, V <sub>GS</sub> =0V	-30			V	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}$ =-30V, $V_{GS}$ =0V			-1		
		$V_{DS}$ =-30V, $V_{GS}$ =0V, $T_{J}$ =55°C		K	-5	μΑ	
Gate-Body Leakage Current	$I_{GSS}$	$V_{DS}$ =0V, $V_{GS}$ =±20V			±100	nA	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=-250\mu A$	-1.4	-1.9	-2.4	V	
On-State Drain Current	I <sub>D(ON)</sub>	$V_{DS}$ =-10V , $V_{GS}$ =-5V	-20			A	
		V <sub>GS</sub> =-10V, I <sub>D</sub> =-5A			52		
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	$V_{GS}$ =-10V, $I_D$ =-5A, $T_J$ =125°C			70	$m\Omega$	
		$V_{GS}$ =-4.5V, $I_{D}$ =-4A	7		87		
Forward Transconductance	$\mathbf{g}_{ extsf{FS}}$	$V_{DS}$ =-5V, $I_D$ =-5A		10		S	
Diode Forward Voltage	$V_{SD}$	$I_S=-1A$ , $V_{GS}=0V$		-0.7	-1	V	
Maximum Body-Diode Continuous Current	$I_S$				-2.5	A	
Dynamic Parameters							
Input Capacitance	$C_{iss}$			520			
Output Capacitance	$C_{oss}$	$V_{GS}$ =0V, $V_{DS}$ =-15V, f=1MHz		100		pF	
Reverse Transfer Capacitance	$C_{rss}$			65			
Gate Resistance	R <sub>g</sub>	$V_{GS}$ =0V, $V_{DS}$ =0V, f=1MHz	3.5	7.5	11.5	Ω	
Switching Parameters							
Total Cate Charge	Q <sub>g</sub> (10V)	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V, I <sub>D</sub> =-5A		9.2	11		
Total Gate Charge	Q <sub>g</sub> (4.5V)			4.6	6	nC	
Gate Source Charge	$Q_{\mathrm{gs}}$	V GS10 V, V DS13 V, ID3A		1.6			
Gate Drain Charge	$Q_{\mathrm{gd}}$			2.2			
Turn-On Delay Time	$t_{D(on)}$			7.5			
Turn-On Rise Time	$t_{\mathrm{r}}$	$V_{GS}$ =-10V, $V_{DS}$ =-15V, $R_L$ =3 $\Omega$ ,		5.5		na	
Turn-Off Delay Time	$t_{D(off)}$	$R_{GEN}=3\Omega$		19		ns	
Turn-Off Fall Time	$t_{\mathrm{f}}$			7			
Body Diode Reverse Recovery Time	$t_{\mathrm{rr}}$	$I_F$ =-5A, $d_i/d_t$ =100A/ $\mu$ s		11		ns	
Body Diode Reverse Recovery Charge	$Q_{rr}$	$I_F$ =-5A, $d_i/d_t$ =100A/ $\mu$ s		5.3		nC	

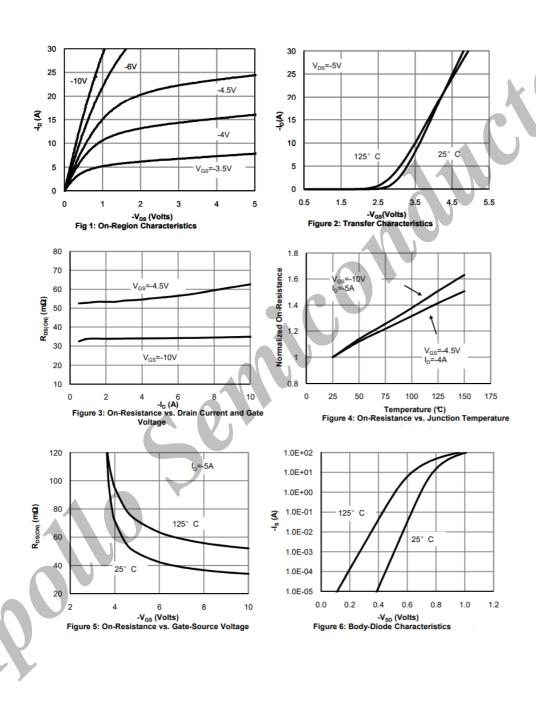
### Ordering Information

Ordering Part Number	Package	MOQ
AP6405	SOT23-6 (SOT163) / TSOP6	3,000 pcs / reel

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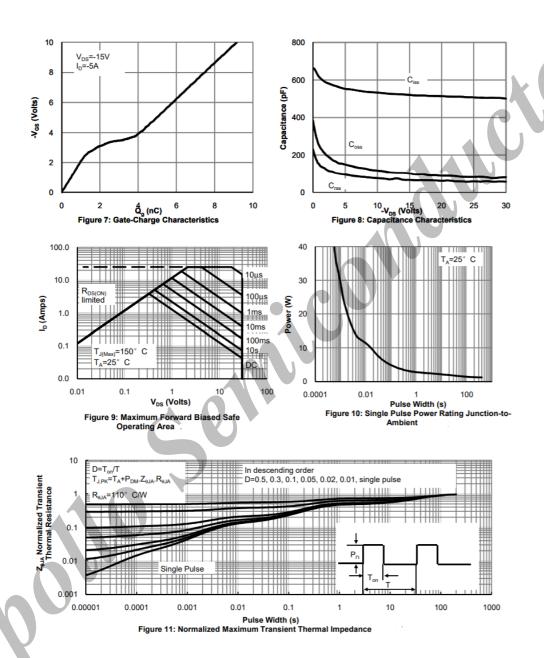
## • Typical Electrical and Thermal Characteristics



Note 1: The static characteristics in Figure 1 to 6 are obtained using <300  $\mu A$  pulses, duty cycle 0.5% max.



### • Typical Electrical and Thermal Characteristics



Note 2: The curves in Figure 9 to 11 are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in2 FR-4 board with 2oz. copper, assuming a maximum junction temperature of TJ(MAX)=150°C. The SOA curve provides a single pulse rating.



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